

PSMN045-100HL

N-channel 100 V, 45 mOhm, logic level MOSFET in LFPAK56D using TrenchMOS technology

26 September 2022

Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology.

2. Features and benefits

- High peak drain current I_{DM}
- Copper clip and flexible Leads
- High operating junction temperature T_i = 175 °C
- Superior reliability
- Low body diode reverse recovery charge Q_r

3. Applications

- · Synchronous rectifier
- Forward and flyback converter
- Industrial drive
- Power management system
- Uninterruptible Power Supply (UPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	21	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	53	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics FET1 and FET2					'	_
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 12$		-	38.3	45	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 175 ^{\circ}\text{C}; Fig. 12; Fig. 13}$		-	103	124	mΩ
Dynamic ch	naracteristics FET1 and FE	T2					
Q _{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V;		-	7.3	-	nC
Q _{G(tot)}	total gate charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	18.5	-	nC
Avalanche	ruggedness FET1 and FET	2				,	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$I_D = 21 \text{ A; } V_{sup} \le 100 \text{ V; } V_{GS} = 5 \text{ V;}$ $T_{j(init)} = 25 \text{ °C; } Fig. 4$	[1] [2]	-	-	48	mJ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain d	Source-drain diode FET1 and FET2						
Q _r		$I_S = 5 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{GS} = 0 \text{ V; } V_{DS} = 50 \text{ V; } T_j = 25 \text{ °C}$		-	42.9	-	nC

- [1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1	1 2 3 4	S1 G1 S2 G2
8	D1	drain1	LFPAK56D; Dual LFPAK (SOT1205)	mbk725

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PSMN045-100HL	· ·	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN045-100HL	45RL10H

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1] [2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	53	W

Symbol	Parameter	Conditions		Min	Max	Unit
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	21	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	15	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	83	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain	diode FET1 and FET2			'		
Is	source current	T _{mb} = 25 °C		-	21	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	83	Α
Avalanche rug	gedness FET1 and FET2				'	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$I_D = 21 \text{ A; } V_{sup} \le 100 \text{ V; } V_{GS} = 5 \text{ V;}$ $T_{j(init)} = 25 \text{ °C; } Fig. 4$	[3] [4]	-	48	mJ

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering T_j and or V_{GS} .
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

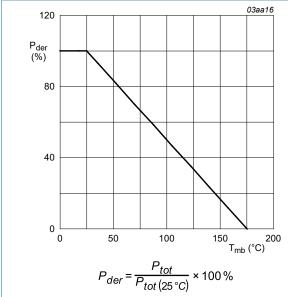


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

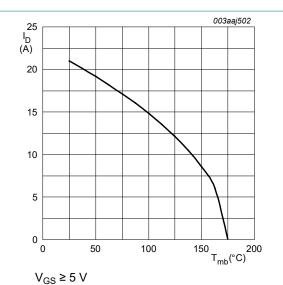
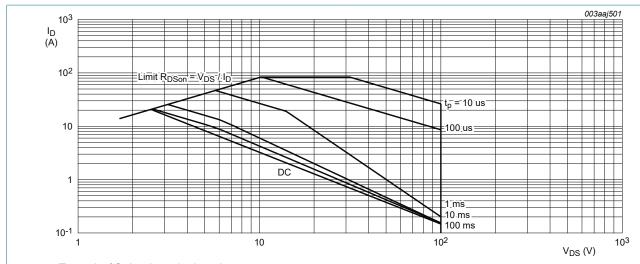


Fig. 2. Continuous drain current as a function of mounting base temperature

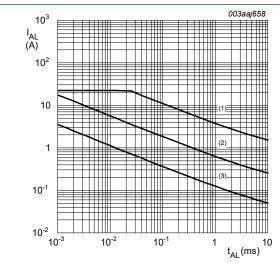
Nexperia PSMN045-100HL

N-channel 100 V, 45 mOhm, logic level MOSFET in LFPAK56D using TrenchMOS technology



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain current as a function of drain-source voltage



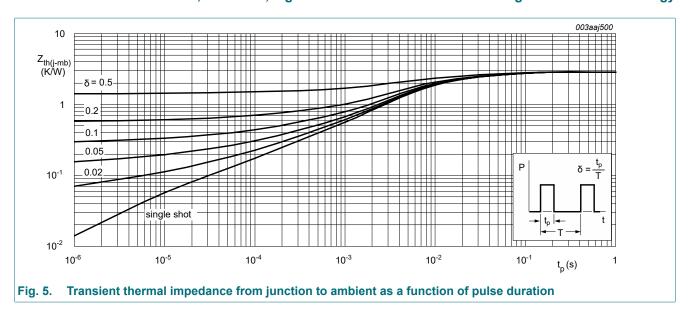
(1) $T_{j \text{ (init)}} = 25 \text{ °C}$; (2) $T_{j \text{ (init)}} = 150 \text{ °C}$; (3) Repetitive Avalanche

Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	2.84	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2			<u> </u>		
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 10;$ Fig. 11	1.4	1.7	2.1	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10; Fig. 11	-	-	2.45	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	38.3	45	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12;</u> <u>Fig. 13</u>	-	103	124	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	35.3	42	mΩ
Dynamic ch	naracteristics FET1 and FE	T2		'		
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	18.5	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	3.5	-	nC
Q_{GD}	gate-drain charge		-	7.3	-	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	1614	2152	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	113	136	pF
C _{rss}	reverse transfer capacitance		-	72	99	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 80 \text{ V}; R_L = 16 \Omega; V_{GS} = 5 \text{ V};$	-	10.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$; $T_j = 25 ^{\circ}C$	-	18.1	-	ns

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _{d(off)}	turn-off delay time			-	26.6	-	ns
t _f	fall time			-	17.5	-	ns
Source-drai	n diode FET1 and FET2		•				
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 17$		-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	29.6	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}; T_j = 25 \text{ °C}$		-	42.9	-	nC

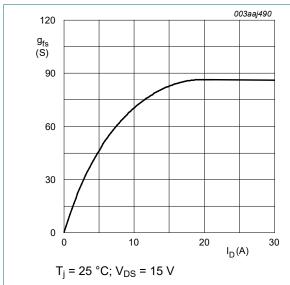


Fig. 6. Forward transconductance as a function of drain current; typical values

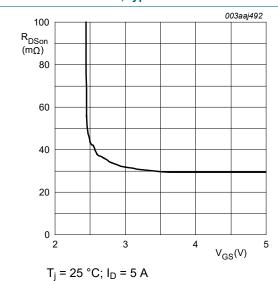


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

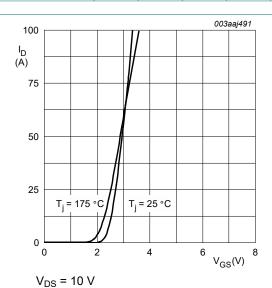
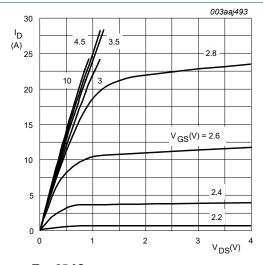


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



T_j = 25 °C

Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

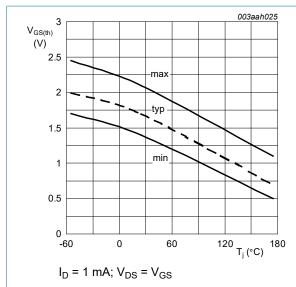


Fig. 10. Gate-source threshold voltage as a function of junction temperature

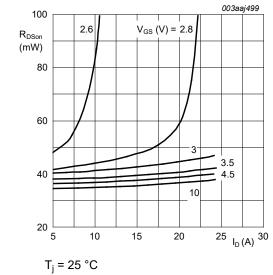


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

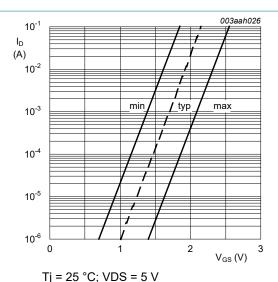


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

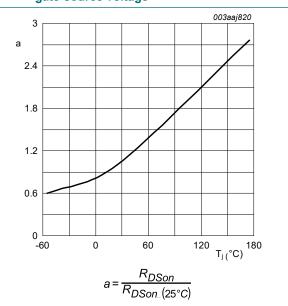


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

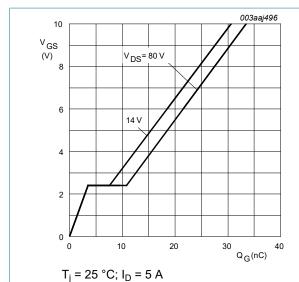


Fig. 14. Gate-source voltage as a function of gate charge; typical values

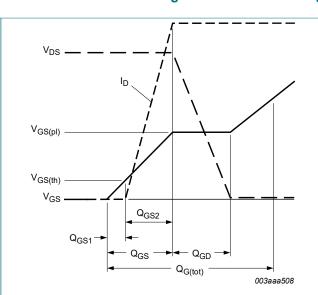


Fig. 15. Gate charge waveform definitions

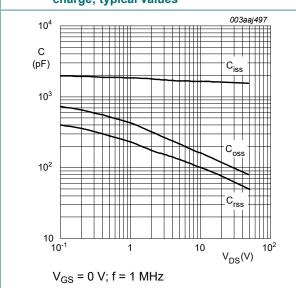
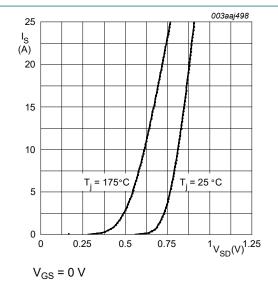


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values



voltage; typical values

11. Package outline

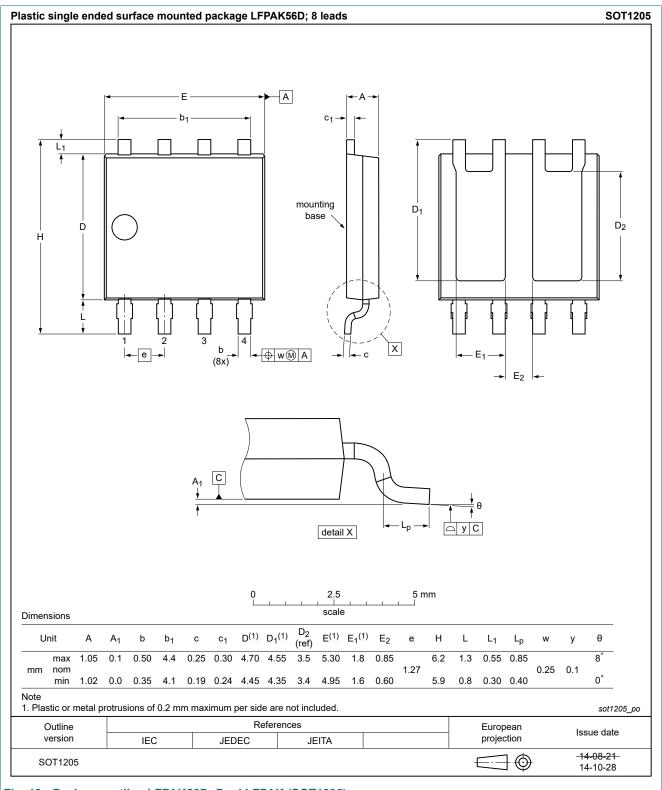
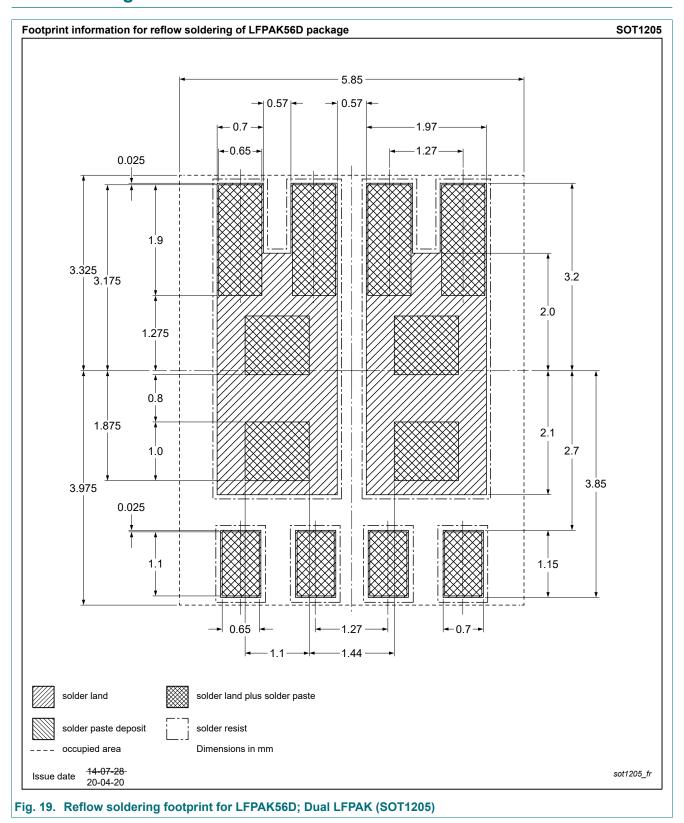


Fig. 18. Package outline LFPAK56D; Dual LFPAK (SOT1205)

12. Soldering



13. Legal information

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Document status [1][2]	Product status [3]	Definition
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